

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE: 6PT1606N1T \* \*

CHIP SIZE	0.36 * 0.36mm
WAFER SIZE	6inch
POSSIBLE DIE PER WAFER	119,000pcs

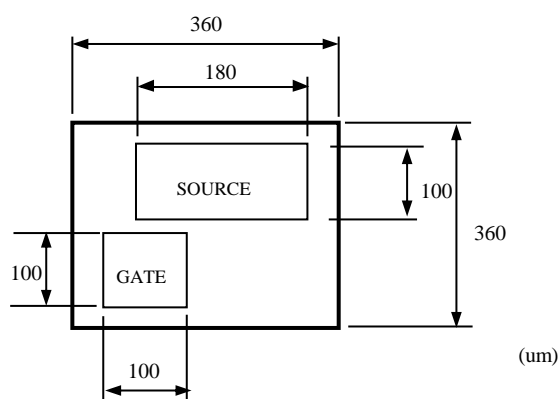
Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	V <sub>DSS</sub>	50	V
Gate-source voltage	V <sub>GSS</sub>	±8	V

PROBING SPEC (Ta=25°C)

No	MODE	LIMIT			UNIT	CONDITIONS
		MIN.	Typ	MAX.		
1	IGSS			±1	uA	V <sub>G</sub> S=±8V V <sub>D</sub> S=0V
2	IDSS			10	uA	V <sub>D</sub> S=52V V <sub>G</sub> S=0V
3	BVDSS	52			V	ID=100μA
4	V <sub>TH</sub>	0.65		1.05	V	ID=250μA
5	R <sub>DS(on)</sub>		3.5	5	Ω	V <sub>G</sub> S=4.0V, ID=100mA
6	Y <sub>fs</sub>	180			mS	V <sub>D</sub> S=10V Id=100mA

※ Built-in ZD between Gate and Source.



NOTE: